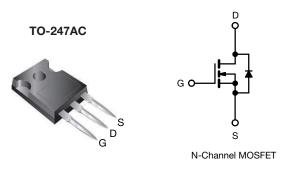
**Vishay Siliconix** 



# **Power MOSFET**



PRODUCT SUMMARY			
V <sub>DS</sub> (V) at T <sub>J</sub> max.	550		
R <sub>DS(on)</sub> typ. (Ω) at 25 °C	$V_{GS} = 10 V$	0.234	
Q <sub>g</sub> max. (nC)	116		
Q <sub>gs</sub> (nC)	22		
Q <sub>gd</sub> (nC)	3	5	
Configuration	Single		

### FEATURES

- Low figure-of-merit (FOM) Ron x Qa
- Low effective capacitance (C<sub>o(er)</sub>)
- · Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	IRFP460HPBF

<b>ABSOLUTE MAXIMUM RATINGS (T</b> <sub>C</sub>	= 25 °C, unl	ess otherwis	se noted)		
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V <sub>DS</sub>	500	v
Gate-source voltage			V <sub>GS</sub>	± 30	v
Continuous drain current ( $T_{1} = 150 \ ^{\circ}C$ )	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C T <sub>C</sub> = 100 °C	1	20	
Continuous drain current $(1_j = 150^{\circ} C)$	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 100 °C	Ι <sub>D</sub>	13	А
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	54	
Linear derating factor				2.6	W/°C
Single pulse avalanche energy <sup>b</sup>			E <sub>AS</sub>	621	mJ
Maximum power dissipation			PD	329	W
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Drain-source voltage slope $T_J = 125 \text{ °C}$			66	1//22	
Reverse diode dv/dt <sup>d</sup>		•	dv/dt	0.5	V/ns
Soldering recommendations (peak temperature) <sup>c</sup>	For	10 s		260	°C

#### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature

- b.  $V_{DD}$  = 120 V, starting  $T_J$  = 25 °C, L = 4.3 mH,  $R_g$  = 25  $\Omega,$   $I_{AS}$  = 17 A
- c. 1.6 mm from case
- d.  $I_{SD} \leq I_D$ , di/dt = 100 A/µs, starting  $T_J$  = 25 °C





PARAMETER	SYMBOL	TYP.		MAX.			UNIT	
Maximum junction-to-ambient	R <sub>thJA</sub>	-		40			0 <b>0</b> 00	
Maximum junction-to-case (drain)	R <sub>thJC</sub>	- 0.45			°C/W			
SPECIFICATIONS (T <sub>J</sub> = 25 °C,	unless otherw	ise noted)						
PARAMETER	SYMBOL		T CONDITIO	NS	MIN.	TYP.	MAX.	UNIT
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250	0 μΑ	500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I <sub>D</sub>	) = 1 mA	-	0.56	-	V/°C
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 25	0 μΑ	2.0	-	4.0	V
		,	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Gate-source leakage	I <sub>GSS</sub>	,	V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
		V <sub>DS</sub> =	= 500 V, V <sub>GS</sub> =	= 0 V	-	-	1	
Zero gate voltage drain current	IDSS	V <sub>DS</sub> = 400 V	, V <sub>GS</sub> = 0 V, 1	Г <sub>Ј</sub> = 125 °С	-	-	100	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> =	= 12 A	-	0.234	0.270	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub>	= 10 V, I <sub>D</sub> = 1	2 A	-	9.6	-	S
Dynamic					•	•		
Input capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V,		-	3208	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 100 V,$ f = 1 MHz		-	163	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	17	-		
Effective output capacitance, energy related <sup>a</sup>	C <sub>o(er)</sub>			-	114	-		
Effective output capacitance, time related <sup>b</sup>	C <sub>o(tr)</sub>	$V_{\rm DS} = 0$	V to 480 V, V <sub>0</sub>	<sub>GS</sub> = 0 V	-	206	-	
Total gate charge	Qg				-	77	116	
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A,	V <sub>DS</sub> = 400 V	-	22	-	nC
Gate-drain charge	Q <sub>gd</sub>				-	35	-	
Turn-on delay time	t <sub>d(on)</sub>		•		-	29	58	
Rise time	t <sub>r</sub>	V <sub>DD</sub> =	= 400 V, I <sub>D</sub> = 1	12 A,	-	60	90	
Turn-off delay time	t <sub>d(off)</sub>	V <sub>GS</sub> =	= 10 V, R <sub>g</sub> = 9	.1 Ω	-	67	101	ns
Fall time	t <sub>f</sub>				-	47	94	
Gate input resistance	R <sub>g</sub>	f = 1	MHz, open d	Irain	0.37	0.75	1.5	Ω
Drain-Source Body Diode Characteris								
Continuous source-drain diode current	I <sub>S</sub>	MOSFET sym showing the	bol		-	-	22	
Pulsed diode forward current	I <sub>SM</sub>	integral revers p - n junction			-	-	54	A
Diode forward voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C	C, I <sub>S</sub> = 12 A, \	/ <sub>GS</sub> = 0 V	-	-	1.2	V
Reverse recovery time	t <sub>rr</sub>	-			-	384	768	ns
Reverse recovery charge	Q <sub>rr</sub>		5 °C, I <sub>F</sub> = I <sub>S</sub> =		-	5.1	10.2	μC
Reverse recovery current	I <sub>RRM</sub>	ai/at =	100 A/µs, V <sub>R</sub>	= 25 V	-	26	-	A



**Vishay Siliconix** 

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

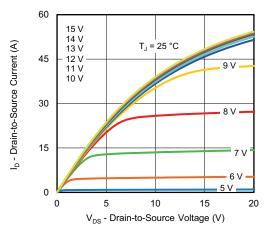


Fig. 1 - Typical Output Characteristics

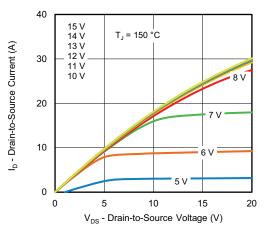


Fig. 2 - Typical Output Characteristics

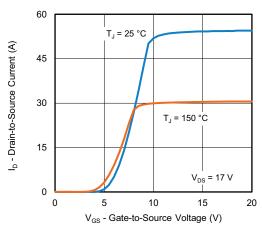


Fig. 3 - Typical Transfer Characteristics

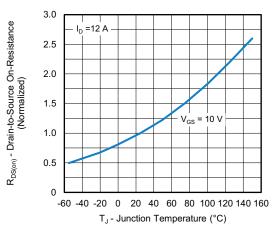


Fig. 4 - Normalized On-Resistance vs. Temperature

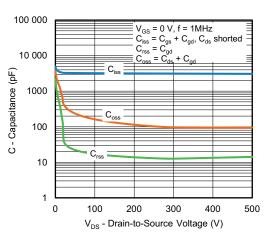
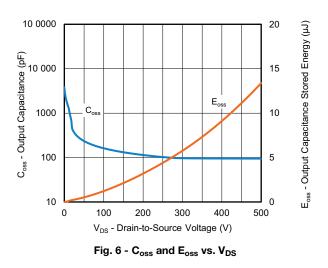


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



3 questions contact: hym@vir Document Number: 92440



Vishay Siliconix

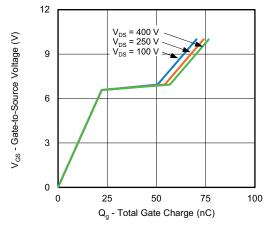


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

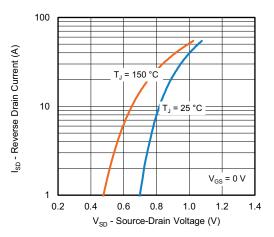


Fig. 8 - Typical Source-Drain Diode Forward Voltage

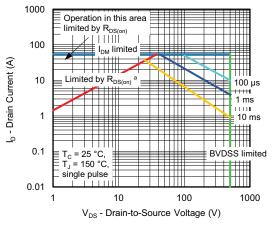


Fig. 9 - Maximum Safe Operating Area

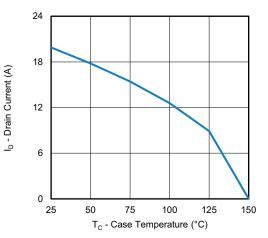


Fig. 10 - Maximum Drain Current vs. Case Temperature

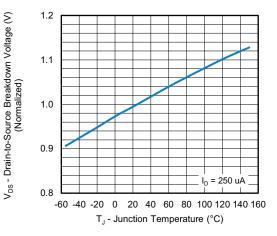
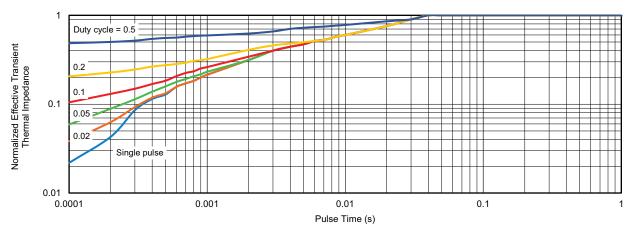


Fig. 11 - Temperature vs. Drain-to-Source Voltage

S22-0722-Rev. A, 22-Aug-2022

4







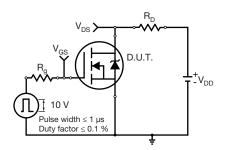


Fig. 13 - Switching Time Test Circuit

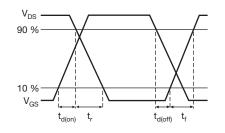


Fig. 14 - Switching Time Waveforms

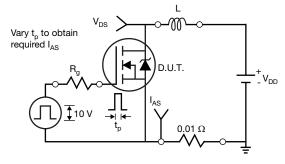
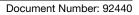


Fig. 15 - Unclamped Inductive Test Circuit

S22-0722-Rev. A, 22-Aug-2022

5



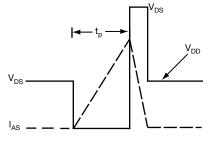


Fig. 16 - Unclamped Inductive Waveforms

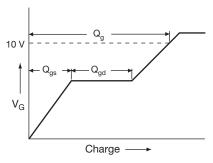
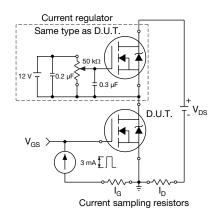


Fig. 17 - Basic Gate Charge Waveform





### **Vishay Siliconix**

#### Fig. 18 - Gate Charge Test Circuit

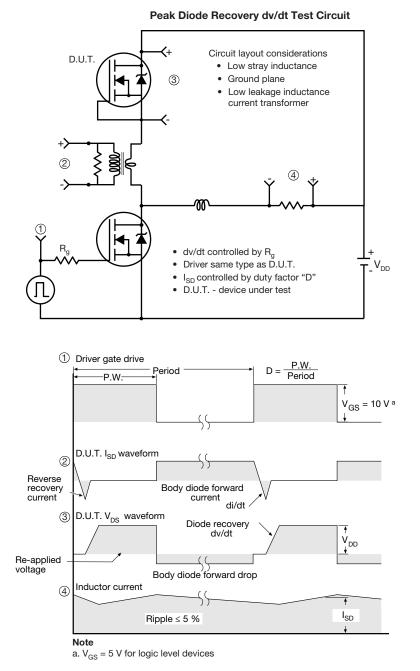


Fig. 19 - For N-Channel

6



www.vishay.com

### Vishay Siliconix

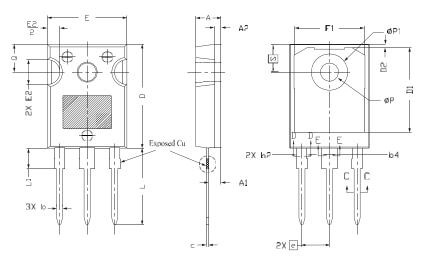
Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?92440</u>.





**TO-247AC (High Voltage)** 

### VERSION 1: FACILITY CODE = 9





	М	ILLIMETERS		
DIM.	MIN.	NOM.	MAX.	NOTES
А	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

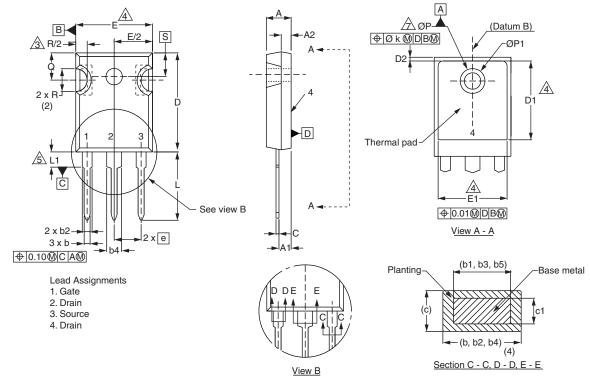
		MILLIMETER	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØР	3.56	3.61	3.65	7
Ø P1		7.19 ref.		
Q	5.31	5.50	5.69	
S		5.51 BSC		

#### Notes

- <sup>(1)</sup> Package reference: JEDEC<sup>®</sup> TO247, variation AC
- (2) All dimensions are in mm
- <sup>(3)</sup> Slot required, notch may be rounded
- <sup>(4)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(5)</sup> Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



### VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
с	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

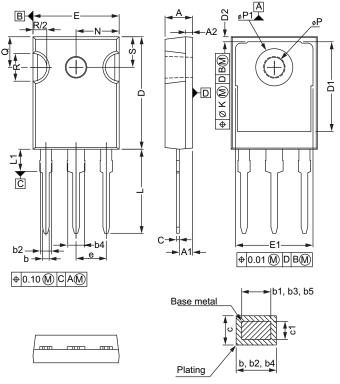
	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- <sup>(2)</sup> Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- <sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC outline TO-247 with exception of dimension c



### VERSION 3: FACILITY CODE = N



	MILLIN	IETERS		MILLIN	<b>IETERS</b>
DIM.	MIN.	MAX.	DIM.	MIN.	MAX
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	е	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

<sup>(2)</sup> Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.